



Schottky Diodes

Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical A : Terminals leads, solderable per J-STD-002 and JESD22-B102

Polarity: As marked

Maximum Ratings (T_a=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR4045CT
Device marking code			MBR4045CT
Repetitive Peak Reverse Voltage	V _{RRM}	V	45
Average Rectified Output Current @60Hz sine wave, R-load, T _c =126	I _O	A	40
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _a =25	I _{FSM}	A	300
Current Squared Time @1ms t 8.3ms T _j =25	I ² t	A ² s	373
Storage Temperature	T _{stg}		-55 ~ +150
Junction Temperature	T _j		-55 ~ +150

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Peak Forward Voltage	V _{FM}		I _{FM} =20.0A T _j =125	-	-	0.52
			V _{RM} =V _{RRM} T _j =25	-	-	0.2
DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} T _j =25	-	-	0.2
	I _{RRM2}		V _{RM} =V _{RRM} T _j =125	-	-	50
Junction capacitance	C _j	pF	1MHz and Applied Reverse Voltage of 4.0 V.D.C	600	900	1300

Note1:Pulse test:300uS pulse width,1% duty cycle

Note2:Pulse test:pulse width 40mS

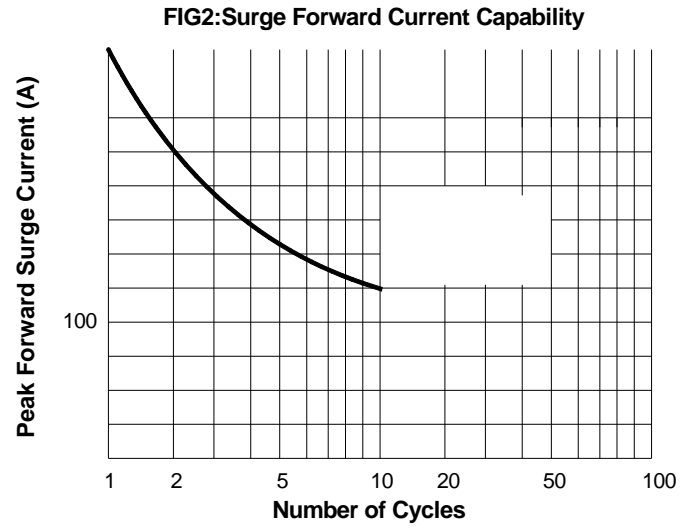


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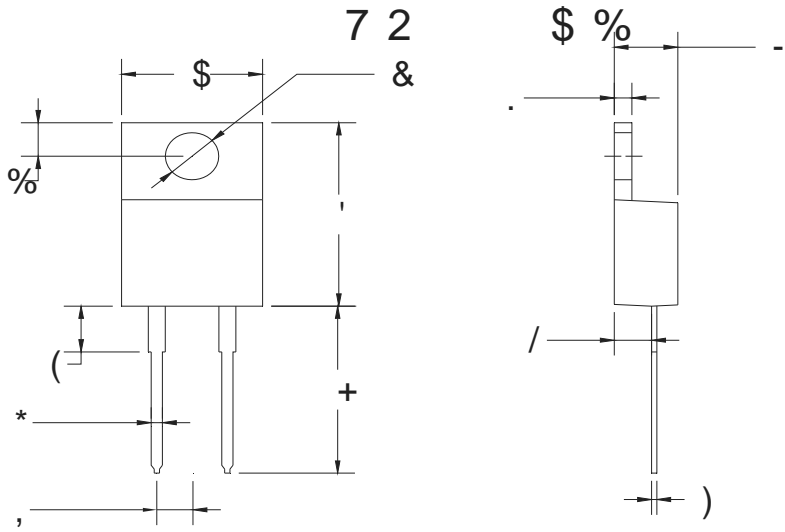
Thermal Characteristics $T_a=25$ Unless otherwise specified

PARAMETER		SYMBOL	UNIT	MBR4045CT
Thermal Resistance	Between junction and ambient	R_{J-A}	/W	60.0
	Between junction and case	R_{J-C}	/W	2.0

Characteristics (Typical)



v2XWOLQH 'LPHQVLRQV





MBR4045CT

Disclaimer

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